

Rev.F Apr.-2017

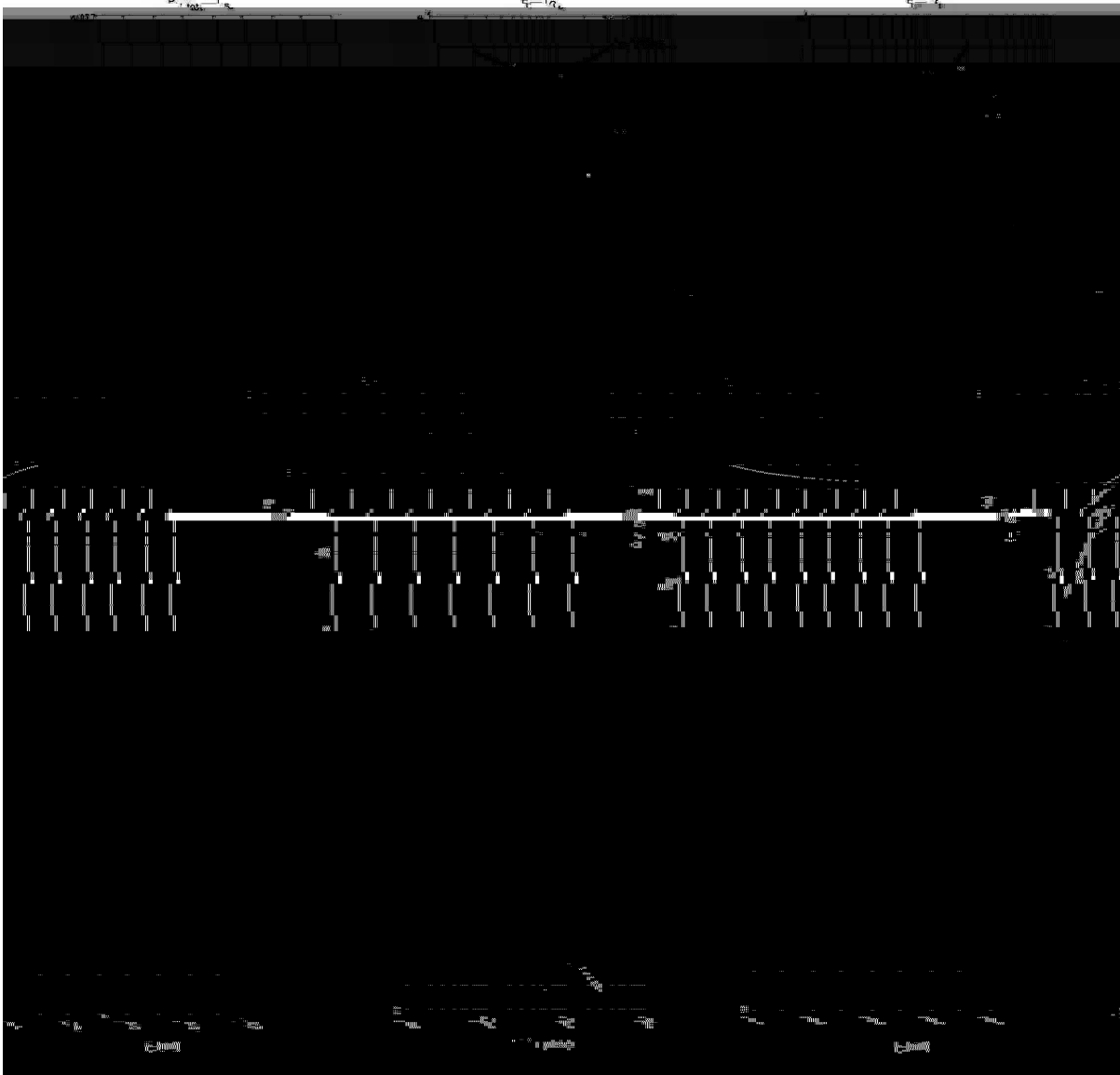
JF K\$) \* E GE Silicon NPN transistor in a SOT-23 Plastic Package.

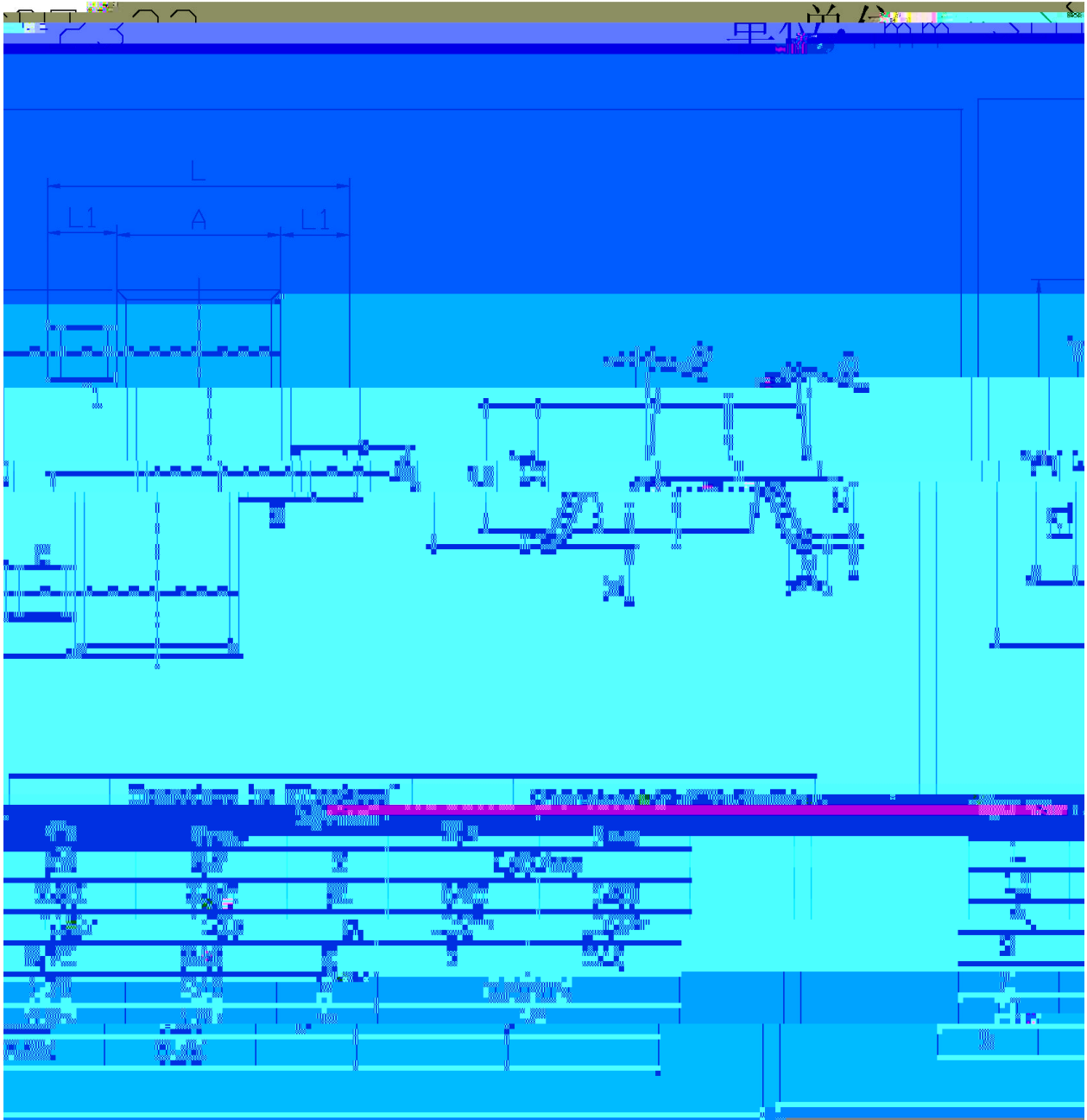
# #

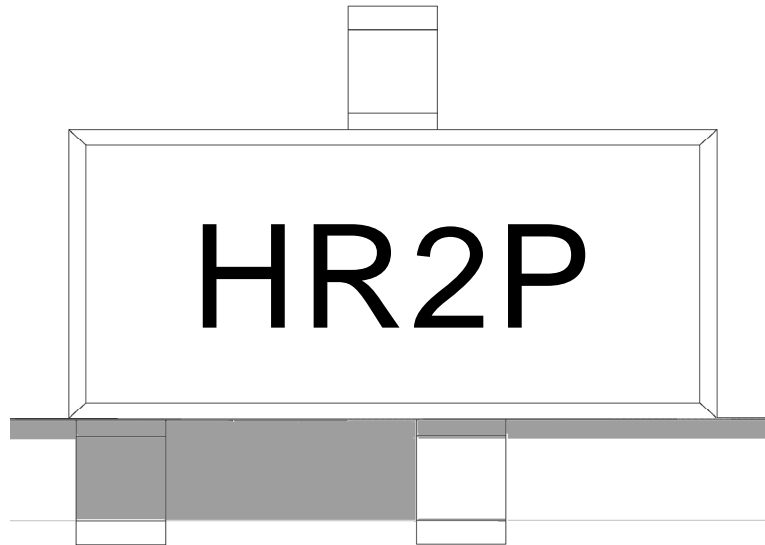
High power gain, low noise figure, very low intermodulation distortion.

RF wideband amplifiers and oscillators.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	15	V

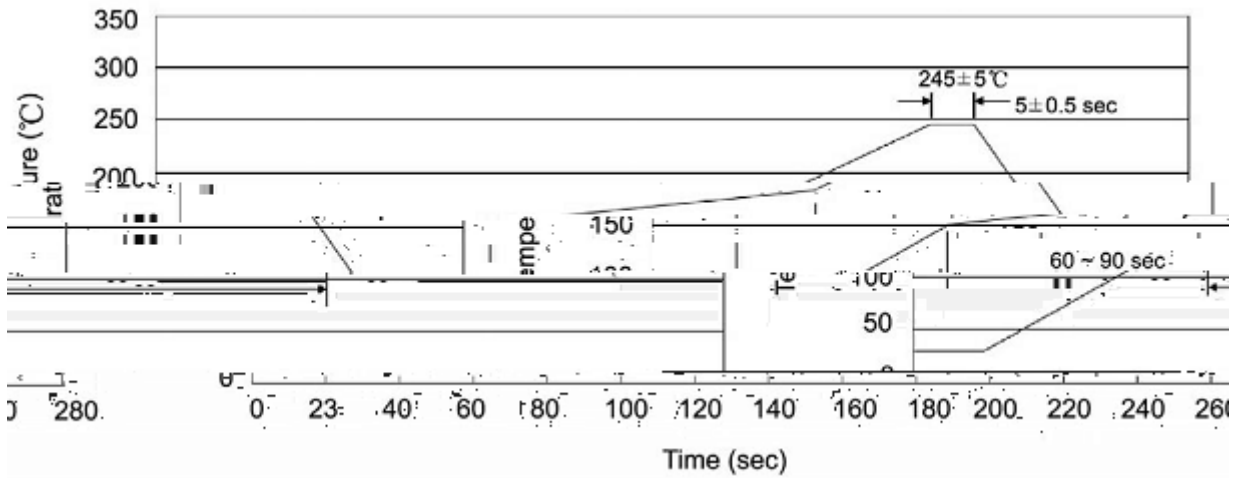






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) I G  
Note:  
H: Company Code.  
2RP: Product Type Code.

### Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- |   |        |     |            |          |   |
|---|--------|-----|------------|----------|---|
| 1 | 25     | 150 | 60         | 90sec;   | 1.Preheating:25~150 , Time:60~90sec.      |
| 2 | 245..5 |     | 5..0.5sec; |          | 2.Peak Temp.:245..5 , Duration:5..0.5sec. |
| 3 |        |     | 2          | 10 /sec. | 3. Cooling Speed: 2~10 /sec.              |

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